

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	3	kV
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ELECTRICAL CHARACTERISTICS (at $T_j=25$ unless otherwise specified)

Symbol	Test Condition	Q	Unit	Value
I_{GT}	$V_D=12V$ $R_L=33\Omega$	-	MAX.	10
V_{GT}		-	MAX.	1
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	-	MIN.	0.2
I_L	$I_G=1.2I_{GT}$	-	MAX.	20
		-		35
I_H	$I_T=100mA$		MAX.	15
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	500
$(dI/dt)_c$	$(dV/dt)_c=10V/\mu s$, $T_j=125$		MIN.	2.5
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2.5
t_{off}				25

STATIC CHARACTERISTICS

Symbol	Parameter	Unit	Value	Condition
V_{TM}	$I_{TM}=5A$ $t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.78	V
R_D	Dynamic resistance	$T_j=125$	190	$m\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.25	mA

THERMAL RESISTANCES

Symbol	Parameter	Unit	Value
$R_{th(j-c)}$	junction to case (AC)	$^{\circ}C/W$	17
$R_{th(j-a)}$	junction to ambient (AC)	$^{\circ}C/W$	60

ORDERING INFORMATION

J	ST	236	V	-800	SW
JieJie Microelectronics Co., Ltd.	Triacs	$I_T(RMS):4A$	$V:SOT-223$	$800:V_{DRM}/V_{RRM} \quad 800V$	$SW:I_{GT1-3} \quad 10mA$

MARKING

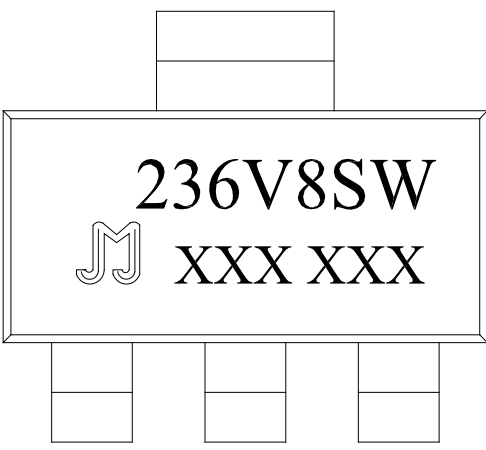
	<u>XXX XXX</u> LOT NO.
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FIG.1: Maximum power dissipation versus RMS on-state current

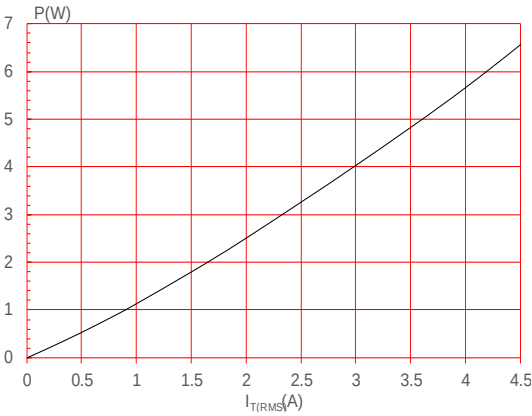


FIG.2: RMS on-state current versus case temperature

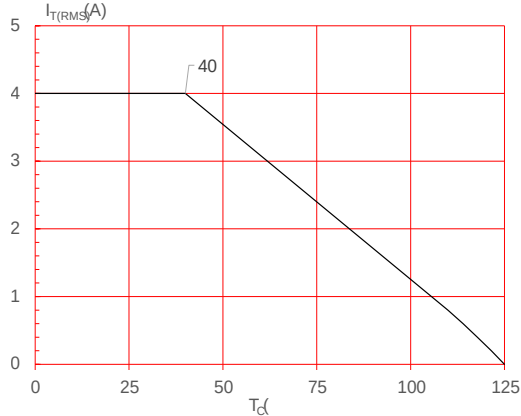


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

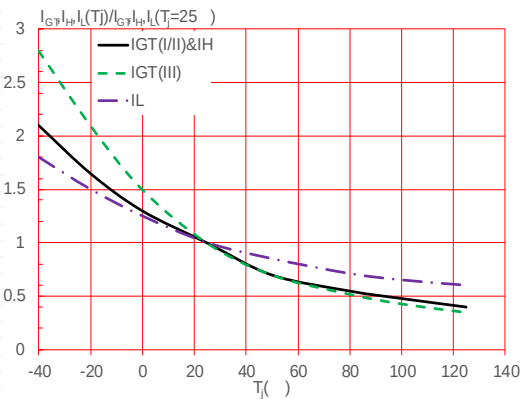
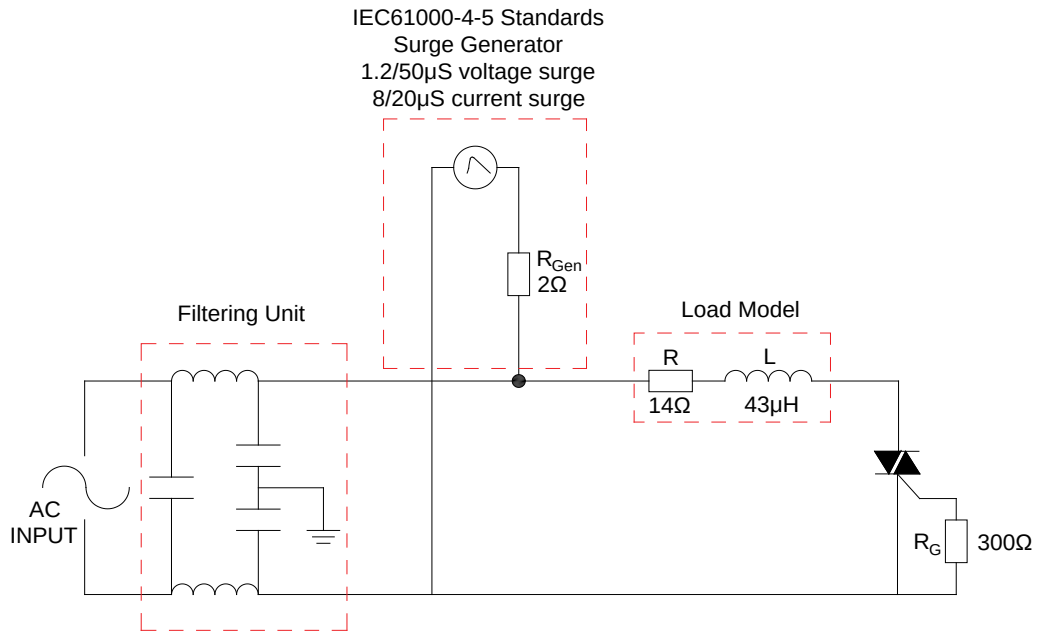


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



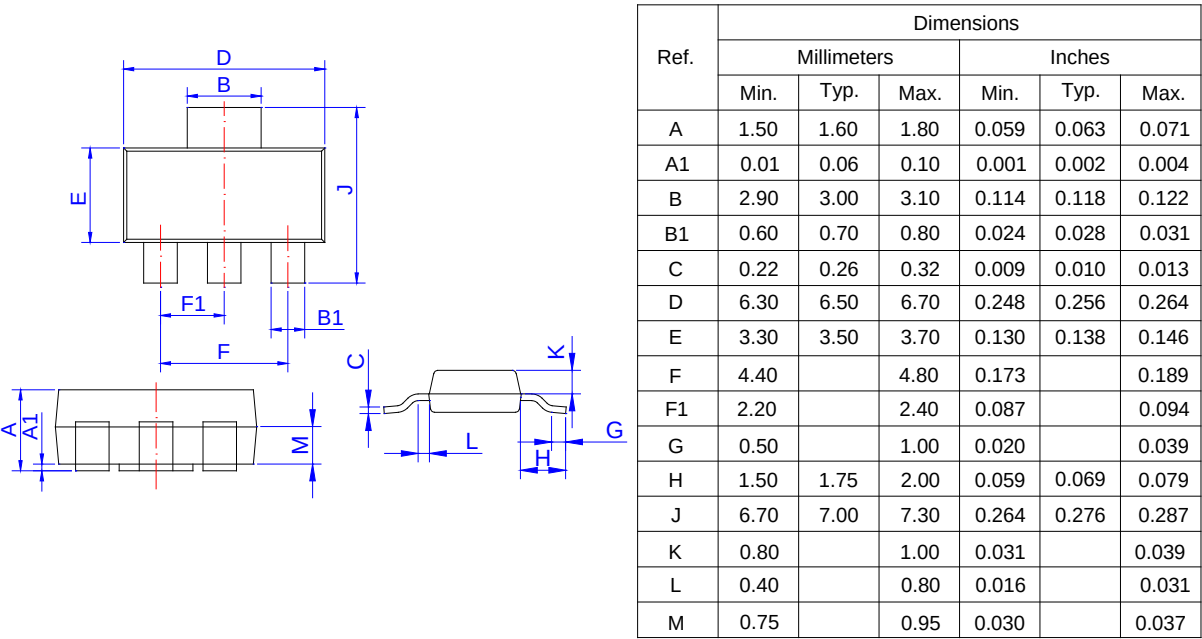
ORDERING INFORMATION

Order No.	V _{DRM} /V _{RRM} (V)	IGT (ms)	Pkg	Qty (pcs)	Delivery lead time
		- -			
JST236V800SW	800	10	SOT-223	4,000	1 Week

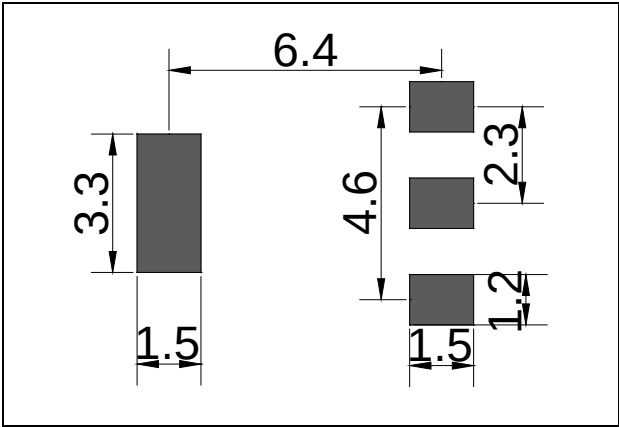
Revision History

Date	Revision	Changes
Apr.11, 2025	A.1.0	Last updated

PACKAGE MECHANICAL DATA



FOOTPRINTSOT223 (dimensions in mm)



DELIVERY MODE

Ref.	Dimensions
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